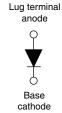


HEXFRED® Ultrafast Soft Recovery Diode, 180 A





HAL	F-P	AK	(D-6	7)

FEATURES

- Very low Q_{rr} and t_{rr}
- Designed and qualified for industrial level
- Material categorization:
 For definitions of compliance please see www.vishav.com/doc?99912



RoHS COMPLIANT

BENEFITS

- · Reduced RFI and EMI
- · Reduced snubbing

DESCRIPTION

HEXFRED® diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and dl_F/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

PRODUCT SUMMARY					
180 A					
400 V					
200 A at 100 °C					
HALF-PAK (D-67)					
Single diode					

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V _R		400	V	
Continuous forward current		T _C = 25 °C	395		
Continuous forward current	l _F	T _C = 100 °C	200	Α	
Single pulse forward current	I _{FSM}	Limited by junction temperature	1200		
Non-repetitive avalanche energy	E _{AS}	$L = 100 \mu H$, duty cycle limited by maximum T_J	1.4	mJ	
Maximum navver dissination	P _D	T _C = 25 °C	657	W	
Maximum power dissipation		T _C = 100 °C	263] vv	
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		400	-	-	
		I _F = 180 A		-	1.08	1.46	V
Maximum forward voltage	V_{FM}	I _F = 360 A	See fig. 1	-	1.22	1.8	
		I _F = 180 A, T _J = 125 °C		-	0.99	1.34	
Maximum reverse leakage current	I _{RM}	T _J = 125 °C, V _R = 400 V	See fig. 2	-	-	4	mA
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	370	500	pF
Series inductance	L _S	From top of terminal hole to mounting plane - 6.0 -		nH			



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5	t _{rr}	T _J = 25 °C	$I_F = 135 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	90	140	ns
		T _J = 125 °C		-	280	440	
Peak recovery current See fig. 6	I _{RRM}	T _J = 25 °C		-	9	16	А
		T _J = 125 °C		-	18	32	
Reverse recovery charge See fig. 7	Q _{rr}	T _J = 25 °C		-	300	950	nC
		T _J = 125 °C		-	2650	6300	
Peak rate of recovery current See fig. 8	dI _{(rec)M} /dt	T _J = 25 °C		-	300	-	- A/μs
		T _J = 125 °C		-	290	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T _J , T _{Stg}		-55 to +150	°C	
Maximum thermal resistance, junction to case		R _{thJC}	DC operation See fig. 4		°C/W	
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.05	C/W	
Approximate weight				30	g	
				1.06	OZ.	
Maunting torque	minimum			3 (26.5)		
Mounting torque	maximum			4 (35.4)	N⋅m	
Terminal torque	minimum			3.4 (30)	(lbf · in)	
	maximum			5 (44.2)		
Case style			HALF-PAK mod	ule		

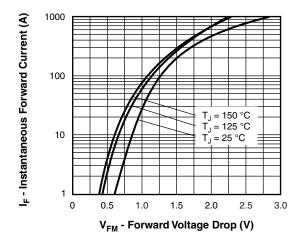


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

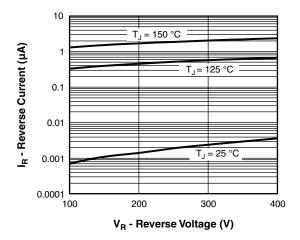


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

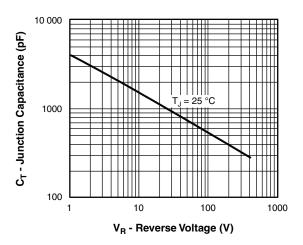


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

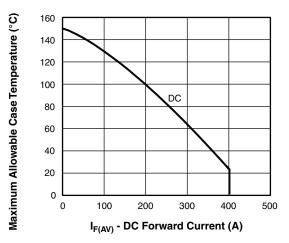


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current

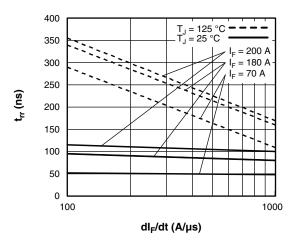


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

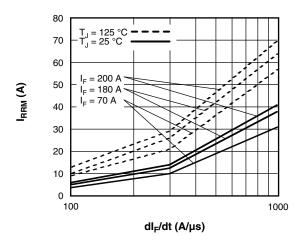


Fig. 6 - Typical Recovery Current vs. dl_F/dt

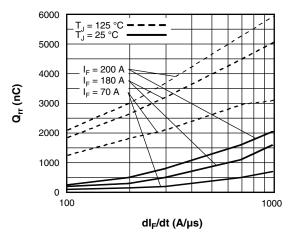


Fig. 7 - Typical Stored Charge vs. dl_F/dt

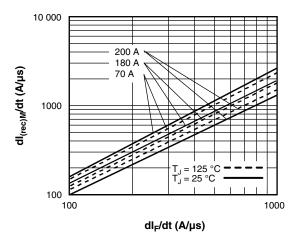


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

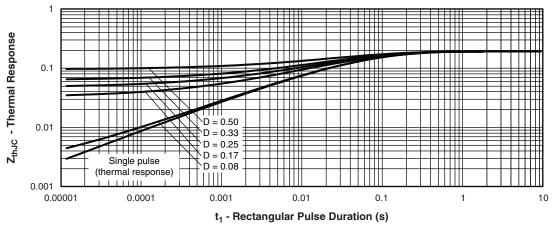


Fig. 9 - Maximum Thermal Impedance Z_{thJC} Characteristics

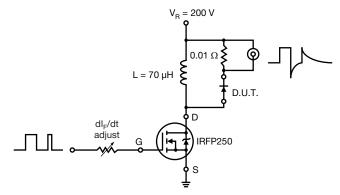
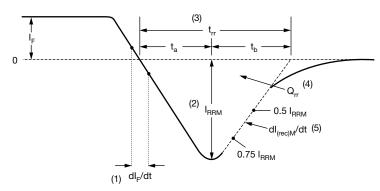


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions



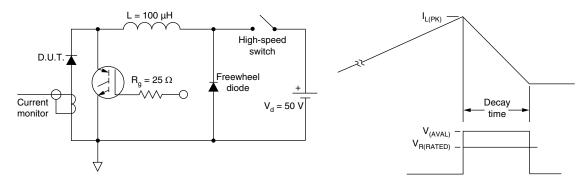
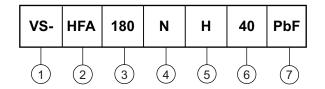


Fig. 12 - Avalanche Test Circuit and Waveforms

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - HEXFRED® family, electron irradiated

Average current rating

4 - N = Not isolated

5 - H = HALF-PAK

6 - Voltage rating (400 V)

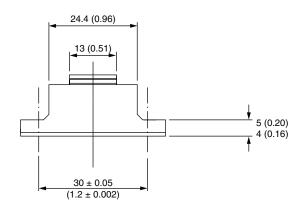
7 - Lead (Pb)-free

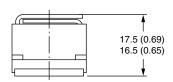
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95020			

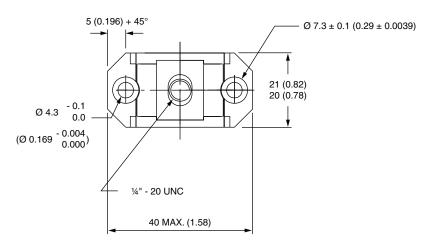


D-67 HALF-PAK

DIMENSIONS in millimeters (inches)









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Vishay

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